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18. The semiconductor device of claim **12**, wherein the elbow angle of the first epitaxial-grown doped layer is not interfacing with the gate structure.

19. The semiconductor device of claim **12**, wherein the second lateral thickness is from about 1 angstrom to about 5 100 angstrom.

20. The semiconductor device of claim **12**, wherein the second lateral thickness is less than a width of the sidewall spacer.

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